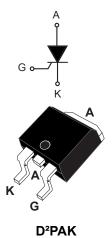


## High temperature 30 A, 600 V D<sup>2</sup>PAK thyristor SCRs



### **Features**

- High junction temperature: T<sub>i</sub> = 150 °C
- High noise immunity dV/dt = 1000 V/µs up to 150 °C
- Gate triggering current I<sub>GT</sub> = 15 mA
- Peak off-state voltage V<sub>DRM</sub>/V<sub>RRM</sub> = 600 V
- High turn-on current rise dI/dt = 100 A/μs
- ECOPACK2 compliant

#### **Applications**

- · General purpose AC line load switching
- · Motorbike voltage regulator circuits
- · Inrush current limiting circuits
- · Motor control circuits and starters
- · Heating resistor control, Solid State Relays
- Lighting

#### **Description**

Thanks to its operating junction temperature up to  $150^{\circ}$ C, the TN3015H-6G SCR in D<sup>2</sup>PAK package offers high thermal performance operation up to 30 A RMS in a compact SMD design.

Its trade-off noise immunity (dV/dt =  $1000 \text{ V/}\mu\text{s}$ ) versus its gate triggering current ( $I_{GT}$  = 15 mA) and its turn-on current rise (dI/dt =  $100 \text{ A/}\mu\text{s}$ ) allows to design robust and compact control circuit for voltage regulator in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances and inrush current limiting circuits.

# Product status TN3015H-6G

Product summary				
Order code	TN3015H-6G			
Package	D <sup>2</sup> PAK			
$V_{DRM}/V_{RRM}$	600 V			
Tj	150 °C			
I <sub>GT</sub>	15 mA			



## 1 Characteristics

Table 1. Absolute maximum ratings (limiting values)

Symbol	Parameter	Value	Unit		
I <sub>T(RMS)</sub>	RMS on-state current (180 ° conduction angle	30	Α		
		T <sub>c</sub> = 127 °C	19		
$I_{T(AV)}$	Average on-state current (180 ° conduction a	T <sub>c</sub> = 134 °C	15	Α	
		T <sub>C</sub> = 141 °C	10		
1	Non repetitive surge peak on state surgest /T			295	
I <sub>TSM</sub>	Non repetitive surge peak on-state current (T	t <sub>p</sub> = 10 ms	270	Α	
l <sup>2</sup> t	I <sup>2</sup> t value for fusing (T <sub>j</sub> initial = 25 °C)	$t_p = t_p = t_p$ initial = 25 °C)		364	A <sup>2</sup> s
11/1/	I <sub>G</sub> = 2 x I <sub>GT</sub> , tr ≤ 100 ns	f = 60 Hz	T <sub>i</sub> = 25 °C	100	A /us
dl/dt	Critical rate of rise of on-state current		1 <sub>j</sub> - 25 C	100	A/µs
V <sub>DRM</sub> /V <sub>RRM</sub>	Repetitive peak off-state voltage	Repetitive peak off-state voltage			V
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state voltage	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25 °C	V <sub>DRM</sub> /V <sub>RRM</sub> +100	V
I <sub>GM</sub>	Peak gate current	t <sub>p</sub> = 20 μs	T <sub>j</sub> = 150 °C	4	Α
P <sub>G(AV)</sub>	Average gate power dissipation	erage gate power dissipation $T_j = 1$		1	W
$V_{RGM}$	Maximum peak reverse gate voltage $T_j = 25$		T <sub>j</sub> = 25 °C	5	V
T <sub>stg</sub>	Storage junction temperature range		-40 to +150	°C	
Tj	Maximum operating junction temperature			-40 to +150	°C

Table 2. Electrical characteristics ( $T_j$  = 25 °C unless otherwise specified)

Symbol	Test conditions				
lot			Min.	6	mA
I <sub>GT</sub>	$V_D = 12 \text{ V}, R_L = 33 \Omega$			15	MA
V <sub>GT</sub>			Max.	1.3	V
$V_{GD}$	$V_D = V_{DRM}, R_L = 3.3 \text{ k}\Omega$ $T_j = 150 \text{ °C}$				V
I <sub>H</sub>	I <sub>T</sub> = 500 mA, gate open Max.				
ΙL	$I_G = 1.2 \times I_{GT}$ Max.				mA
dV/dt	$V_D = 402 \text{ V}$ , gate open $T_j = 150 \text{ °C}$				V/µs
t <sub>gt</sub>	$I_T = 60 \text{ A}, V_D = 600 \text{ V}, I_G = 100 \text{ mA}, (dI_G/dt) \text{ max} = 0.2 \text{ A/µs}$ Typ.				μs
tq	$I_T = 30 \text{ A}, V_D = 402 \text{ V}, (\text{di/dt}) \text{ off} = 30 \text{ A/}\mu\text{s}, V_R = 25 \text{ V}, dV_D/dt = 50 \text{ V/}\mu\text{s}$ $T_j = 150 \text{ °C}$ Type				μs

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#### **Table 3. Static characteristics**

Symbol	Test conditions				
V <sub>TM</sub>	$I_{TM} = 60 \text{ A}, t_p = 380  \mu\text{s}$	T <sub>j</sub> = 25 °C	Max.	1.6	V
V <sub>TO</sub>	Threshold voltage	T <sub>j</sub> = 150 °C	Max.	0.84	V
R <sub>D</sub>	Dynamic resistance	T <sub>j</sub> = 150 °C	Max.	14	mΩ
I <sub>DRM</sub> ,	$V_D = V_{DRM}, V_R = V_{RRM}$	T <sub>j</sub> = 25 °C	Max.	10	μA
I <sub>RRM</sub>	VD - VDRM, VR - VRRM	T <sub>j</sub> = 150 °C		5	mA

#### **Table 4. Thermal parameters**

Symbol	Parameter	Value	Unit	
R <sub>th(j-c)</sub>	Junction to case (DC)	Max.	0.85	°C/W
R <sub>th(j-a)</sub>	Junction to ambient <sup>(1)</sup> $S(1) = 1 \text{ cm}^2$			C/VV

1. S: Copper pad under tab, on PCB FR4

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 $V_{TM}(V)$ 

4.0



#### 1.1 **Characteristics curves**

Figure 1. Maximum power dissipation versus average onstate current P(W) 30 α = 180 α = 120 25 20 15 10 5  $I_{\mathsf{T}(\mathsf{AV})}(\mathsf{A})$ 0 0

Figure 2. Average and DC on-state current versus case temperature  $I_{\underline{\mathsf{T}(\mathsf{AV})}}(\mathsf{A})$ DC 30 25 20 α = 120 15 α = 90  $\alpha = 60^{\circ}$ 10  $\alpha = 30$ 5 0 0 25 50 75 100 125 150

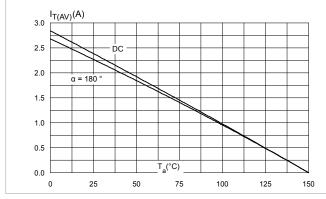
Figure 3. Average and D.C. on state current versus ambient temperature

10

25

10

20



 $I_{TM}(A)$ 1000 100  $V_{t0} = 0.84 \text{ V}$ Rd = 14 m $\Omega$ 

Figure 4. On-state characteristics (maximum values)

Figure 5. Relative variation of thermal impedance junction to case and junction to ambient versus pulse duration

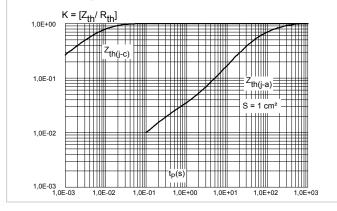
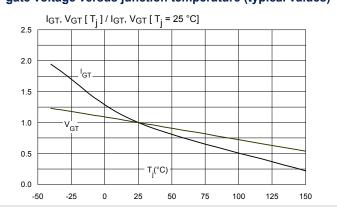


Figure 6. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



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Figure 7. Relative variation of holding and latching current versus junction temperature (typical values)

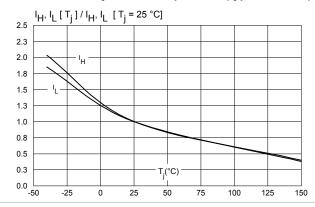


Figure 8. Relative variation of static dV/dt immunity versus junction temperature (typical values)

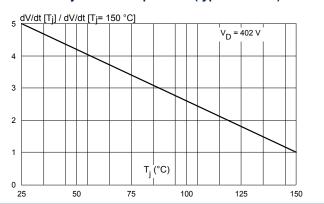


Figure 9. Surge peak on-state current versus number of cycles

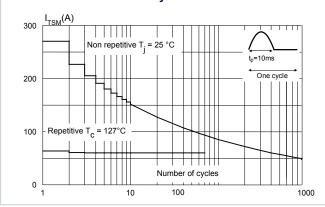


Figure 10. Non repetitive surge peak on-state current for a sinusoidal pulse with width  $t_{\rm p}$  < 10 ms

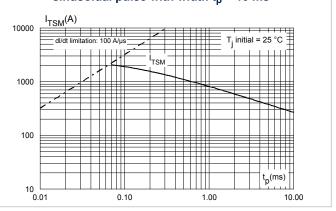


Figure 11. Relative variation of leakage current versus junction temperature

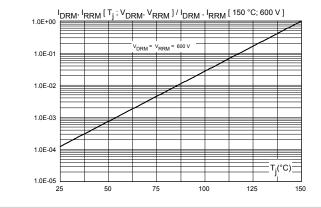
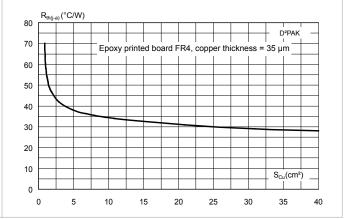


Figure 12. Thermal resistance junction to ambient versus copper surface under tab



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## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

## 2.1 D<sup>2</sup>PAK package information

- ECOPACK®2 compliant
- · Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

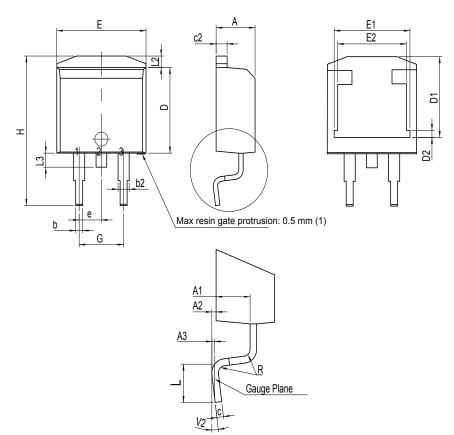


Figure 13. D<sup>2</sup>PAK package outline

(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

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Table 5. D<sup>2</sup>PAK package mechanical data

	Dimensions						
Ref.	Millimeters				Inches <sup>(1)</sup>		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.30		4.60	0.1693		0.1811	
A1	2.49		2.69	0.0980		0.1059	
A2	0.03		0.23	0.0012		0.0091	
A3		0.25			0.0098		
b	0.70		0.93	0.0276		0.0366	
b2	1.25		1.7	0.0492		0.0669	
С	0.45		0.60	0.0177		0.0236	
c2	1.21		1.36	0.0476		0.0535	
D	8.95		9.35	0.3524		0.3681	
D1	7.50		8.00	0.2953		0.3150	
D2	1.30		1.70	0.0512		0.0669	
е	2.54			0.10000			
Е	10.00		10.28	0.3937		0.4047	
E1	8.30		8.70	0.3268		0.3425	
E2	6.85		7.25	0.2697		0.2854	
G	4.88		5.28	0.1921		0.2079	
Н	15		15.85	0.5906		0.6240	
L	1.78		2.28	0.0701		0.0898	
L2	1.27		1.40	0.0500		0.0551	
L3	1.40		1.75	0.0551		0.0689	
R		0.40			0.0157		
V2 <sup>(2)</sup>	0°		8°	0°		8°	

<sup>1.</sup> Dimensions in inches are given for reference only

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<sup>2.</sup> Degrees



Figure 14. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)

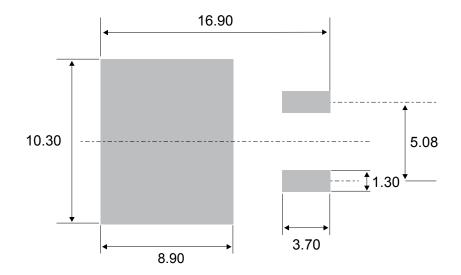
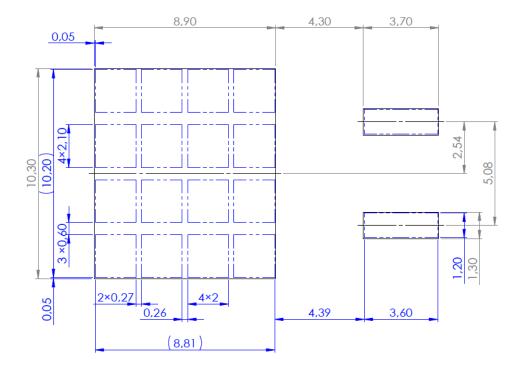


Figure 15. D<sup>2</sup>PAK stencil definitions(dimensions are in mm)

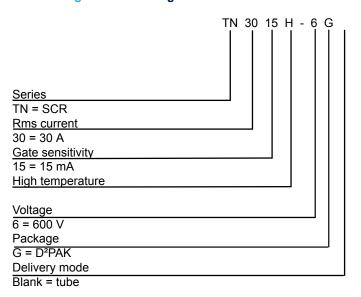


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## 3 Ordering information

Figure 16. Ordering information scheme



**Table 6. Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
TN3015H-6G-TR	TN2045U6C	5H6G D <sup>2</sup> PAK 1.5 g	150	1000	Tape and Reel
TN3015H-6G	TN3015H6G		1.5 g	50	Tube

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## **Revision history**

Table 7. Document revision history

Date	Revision	Changes
05-Jul-2019	1	Initial release.

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